

P-TEOS Wafer Specification

2025/2/28
Nippon Chemi-Con Corporation
Hayakawa

No.	Item	Specification
1	Conductivity Type	P
2	Crystal Orientation	(100) $\pm 1.0^\circ$
3	Resistivity	1.0 ~ 100.0 $\Omega \cdot \text{cm}$
4	Dia Meter	300.0 $\pm$ 0.2mm
5	Thickness	775 $\pm$ 25 μm
6	Surface Finish	Polished
7	Backside Finish	Polished
8	P-TEOS Deposition	1000nm $\pm$ 10%